

Simplified Pull Down scheme

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Presentation Outline

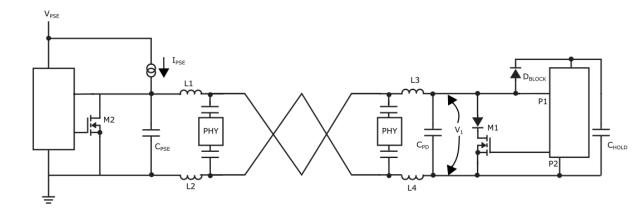
- Few issues with traditional pull down scheme
- Simplified Pull Down scheme
 - FET and blocking devices (diode or another FET)
 - Additional magnetic device for boosting Return Loss
- Additional Benefits of the scheme
 - (Eliminating Kelvin Sensing)
 - Eliminating Voltage Measurement at PD for CRM

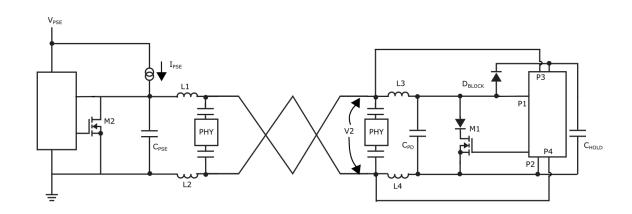


Few Issues with traditional Pull Down scheme

- Inaccuracy due to Power Coupling Network
 - DCR of Coupling Inductors introduces inaccuracy in measured cable resistance

- Need additional connections for Kelvin Sensing
 - Kelvin sensing can be implemented to eliminate the DCR inaccuracy at the cost of more connections



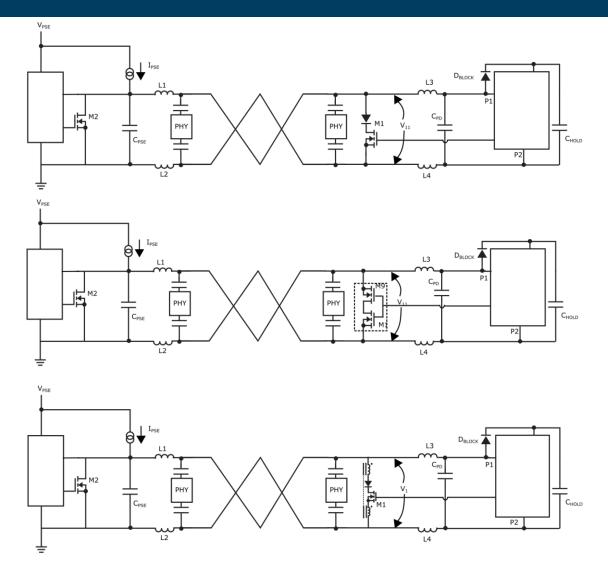




Simplified Pull Down Scheme

- Pull Down FET and reverse blocking device are placed on the Line Side of power coupling inductors
 - Kelvin sensing implemented using connection thru the coupling inductors, without additional connections
- Reverse blocking device can be another back to back connected MOSFET

 Additional magnetic device may be added to boost Return Loss



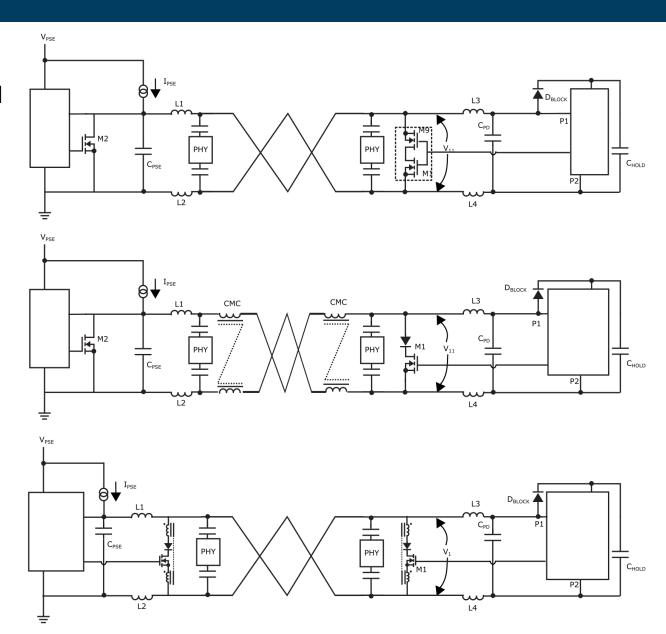


Additional Benefits of the Scheme

- ► Low R_{DS-ON} FETs can be used to Pull Down
 - With a strong enough Pull Down, Voltage at PD PI need not be measured
 - Can be reported as a fixed pre-programmed voltage
 - Also useful in achieving a lower threshold voltage for SCCP

Noise at PI can be reduced by using CMC

Similar schemes can be used at PSE as well





Thank You!

QUESTIONS? FEEDBACK?